

HER501G - HER508G

5.0 AMP. Glass Passivated High Efficient Rectifiers

DO-201AD

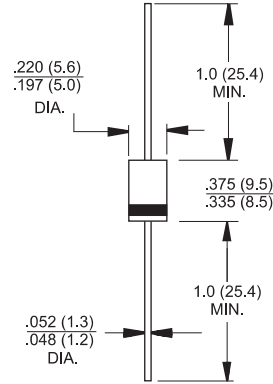


Features

- ✦ Glass passivated chip junction.
- ✦ High efficiency, Low VF
- ✦ High current capability
- ✦ High reliability
- ✦ High surge current capability
- ✦ For use in low voltage, high frequency inverter, free wheeling, and polarity protection application.

Mechanical Data

- ✦ Cases: Molded plastic
- ✦ Epoxy: UL 94V0 rate flame retardant
- ✦ Lead: Pure tin plated, lead free, solderable per MIL-STD-202, method 208 guaranteed
- ✦ Polarity: Color band denotes cathode
- ✦ High temperature soldering guaranteed: 260°C/10 seconds/.375", (9.5mm) lead lengths at 5 lbs., (2.3kg) tension
- ✦ Weight: 1.65grams



Dimensions in inches and (millimeters)

Maximum Rating and Electrical Characteristics

Rating at 25 °C ambient temperature unless otherwise specified.

Single phase, half wave 60 Hz, resistive or inductive load.

For capacitive load, derate current by 20%

Type Number	Symbol	HER 501G	HER 502G	HER 503G	HER 504G	HER 505G	HER 506G	HER 507G	HER 508G	Units
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	50	100	200	300	400	600	800	1000	V
Maximum RMS Voltage	V_{RMD}	35	70	140	210	280	420	560	700	V
Maximum DC Blocking Voltage	V_{DC}	50	100	200	300	400	600	800	1000	V
Maximum Average Forward Rectified Current .375 (9.5mm) lead length @ $T_A = 55^\circ\text{C}$	$I_{(AV)}$	5.0								A
Peak Forward Surge Current, 8.3 ms single half sine-wave superimposed on rated load (JEDEC method)	I_{FSM}	200								A
Maximum Instantaneous Forward Voltage @5.0A	V_F	1.0			1.3		1.7			V
Maximum DC Reverse Current @ $T_a=25^\circ\text{C}$ at Rated DC Blocking Voltage @ $T_a=125^\circ\text{C}$	I_R	10				200				μA μA
Maximum Reverse Recovery Time (Note 1)	T_{rr}	50				75				nS
Typical Junction Capacitance (Note 2)	C_j	100				65				pF
Typical Thermal Resistance	$R_{\theta JA}$	40								$^\circ\text{C}/\text{W}$
Operating Temperature Range	T_J	-65 to +150								$^\circ\text{C}$
Storage Temperature Range	T_{STG}	-65 to +150								$^\circ\text{C}$

- Notes:
1. Reverse Recovery Test Conditions: $I_F=0.5\text{A}$, $I_R=1.0\text{A}$, $I_{RR}=0.25\text{A}$
 2. Measured at 1 MHz and applied reverse voltage of 4.0 V D.C.
 3. Mount on Cu-Pad Size 16mm x 16mm on P.C.B.

RATINGS AND CHARACTERISTIC CURVES (HER501G THRU HER508G)

FIG.1- MAXIMUM FORWARD CURRENT DERATING CURVE

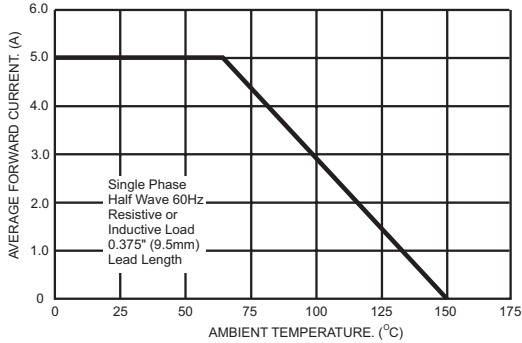


FIG.2- TYPICAL REVERSE CHARACTERISTICS

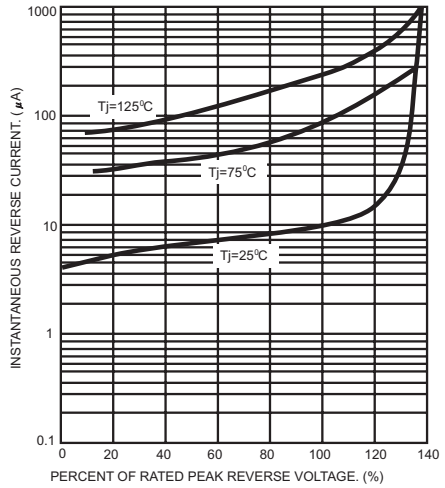


FIG.3- MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

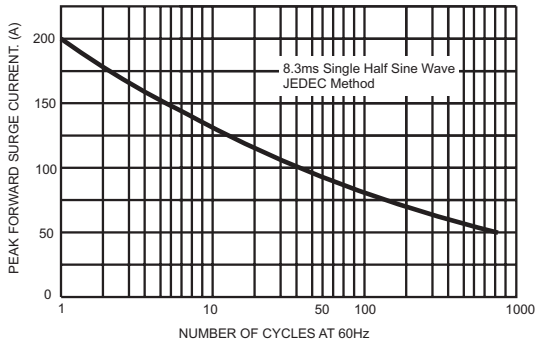


FIG.5- TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

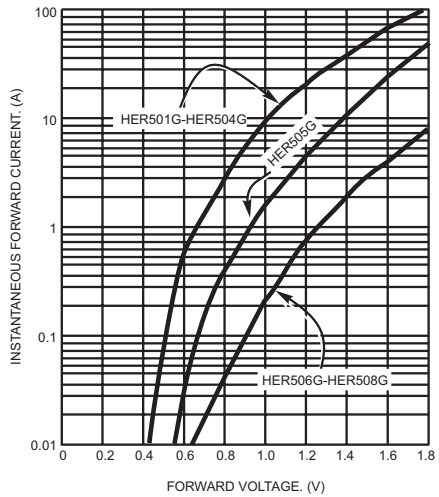


FIG.4- TYPICAL JUNCTION CAPACITANCE

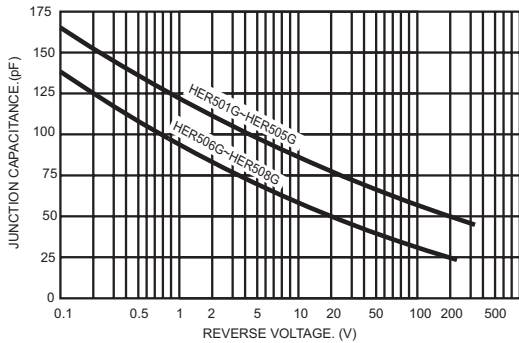
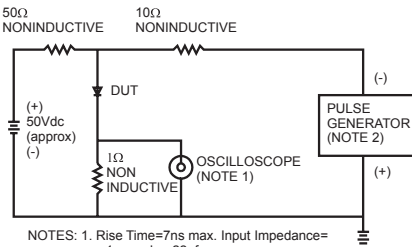


FIG.6- REVERSE RECOVERY TIME CHARACTERISTIC AND TEST CIRCUIT DIAGRAM



- NOTES: 1. Rise Time=7ns max. Input Impedance= 1 megohm 22pf
2. Rise Time=10ns max. Source Impedance= 50 ohms

